GSD10V45S

Ultra-Low VF Surface Mount Schottky Barrier Rectifiers

Product Description

Device optimized for ultra-low forward voltage drop to maximize efficiency in Power Supply applications.

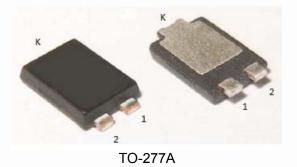
Features

- High Performance Forward Voltage Drop
- Reliable High Temperature Operation
- Softest, fast switching capability
- 150°C Operating Junction Temperature
- Lead Free Finish, RoHS Compliant
- Green Molding Compound (No Br, Sb)

Mechanical Data

- Case : TO-277A
- Molder Plastic : UL Flammability Classification Rating 94V-0
- Device Weight : 0.003 ounces (0.093grams)

Packages



Marking Information

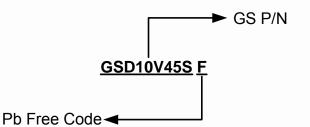
Part Number	Package	Marking	Equivalent Circuit Diagram	
GSD10V45SF	TO-277A	10V45 YM A	PIN K Case PIN1 PIN2	

※ "10V45" GS P/N

% "YM" Date Code & "A" GS Code



Ordering Information



Part Number	Package	Quantity
GSD10V45SF	TO-277A	5000 PCS

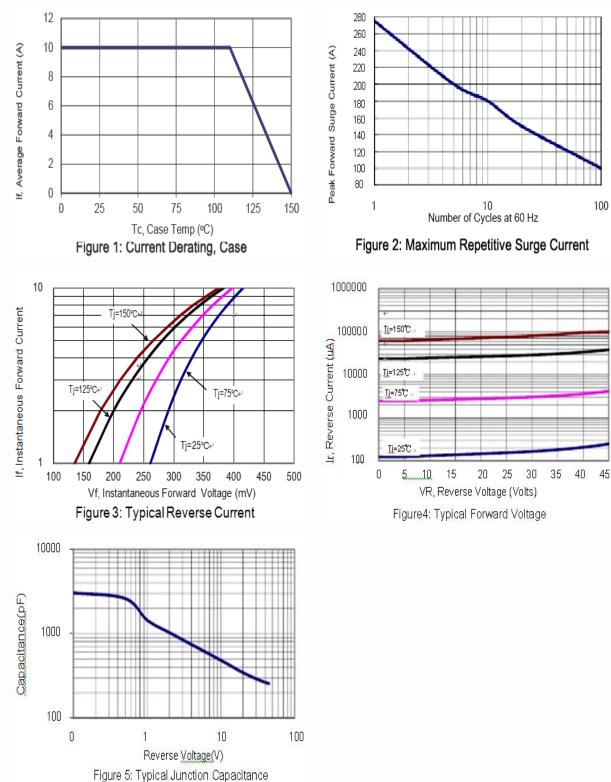
Maximum Ratings and Electrical Characteristics Rating 25°C Ambient Temperature Unless Otherwise Specified.

Symbol	Conditions		Values	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage		45	V
V _{RWM}	Maximum Working Peak Reverse Voltage		45	V
V _{RM}	Maximum DC Blocking Voltage		45	V
V _F *	Instantaneous Forward Voltage At 10A	TJ=25°C	0.47	V
V F	Instantaneous Forward Voltage At 10A	TJ=125°C	0.39~0.42	
Ι _ο	Average Rectified Forward Current (Rated V _R -20Khz Square Wave) - 50% duty cycle		10	А
I _{FSM}	Peak Forward Surge Current - 1/2 60hz		275	Α
I _{RRM}	Peak Repetitive Reverse Surge Current (2uS-1Khz)		2	А
I _R	Instantaneous Reverse Current At V_{RM}	TJ=25°C	0.5	mA
'R		TJ=125°C	100	
dv/dt	Maximum Rate of Voltage Change (at Rated V_R)		10000	V/uS
$R_{ extsf{ heta}JA}$	Typical Thermal Resistance		60	°C/W
TJ	Junction Temperature Range		-40 to +150	°C
T _{STG}	Storage Temperature Range		-40 to +150	°C

* Pulse width < 300 uS, Duty cycle < 2%



Typical Characteristics



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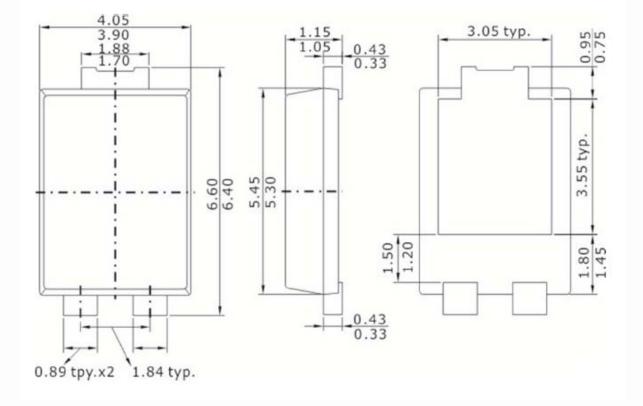
ONDU

GSD10V45S



Package Dimension

TO-277A





NOTICE

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